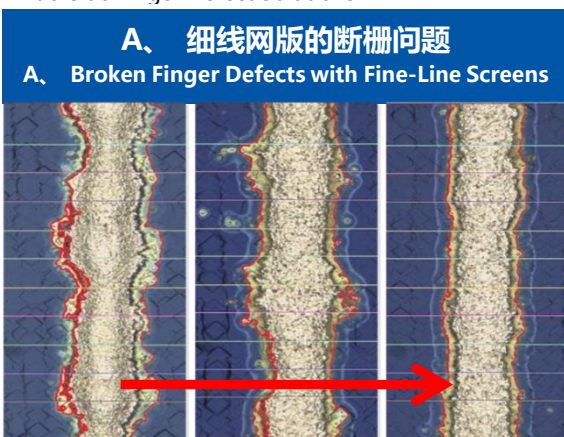


<p>适用场景 Application</p>	<p>匹配 LP、PE、PVD 等多种 Poly 技术路线，可根据背面 poly 层厚薄或结构差异定制 Fit for all kinds of TOPCon deposition methods, either polished or textured wafers</p>
<p>印刷网版 Printing screen</p>	<p>适配 PI 无网结超细线网版、钢版等 PI knotless screen with ultra fine line finger pattern</p>
<p>亮点 Highlight</p>	<ul style="list-style-type: none"> • 优异的 Voc 及 FF 平衡能力，带来更高转换效率 Well-balanced Voc and FF performance for higher conversion efficiency. • 较宽的烧结窗口，在低单耗、低烧温下，依然具有优异的 IV、EL 及可靠性表现 Robust firing window design, maintaining excellent IV, EL and reliability performance at low laydown and low firing temperatures • 兼容 LP、PE、PVD 等多种 Poly 技术路线，定制化匹配不同 Poly 厚度或结构 Compatible with LP, PE, PVD and other Poly deposition routes, with customized solutions for different poly thicknesses and wafer structures • 可兼容背面含 Al₂O₃ 或不含 Al₂O₃ 的两种膜层结构 Adaptable to wafers with or without Al₂O₃ backside passivation layers • 适配超窄线宽印刷，目前兼容 10μm 以上细栅版图 Suitable for ultra-fine line printing, supporting finger patterns down to 10μm • 正常固含及低固含并行的技术路线，可匹配客户端各种降本、提效方案 Both standard and low-solid-content formulations available to support customers' cost reduction and efficiency improvement goals • 快速烘干，且在烧结前后摩擦时均无脱粉问题 Fast drying capability with no powder shedding during friction tests before and after firing • 完美适配激光增强接触优化技术，进一步提升电池转换效率，并与正面工艺匹配，减少 EL 不良 Fully compatible with laser-enhanced contact optimization technology, further improving conversion efficiency and matching front-side processes to reduce EL defect

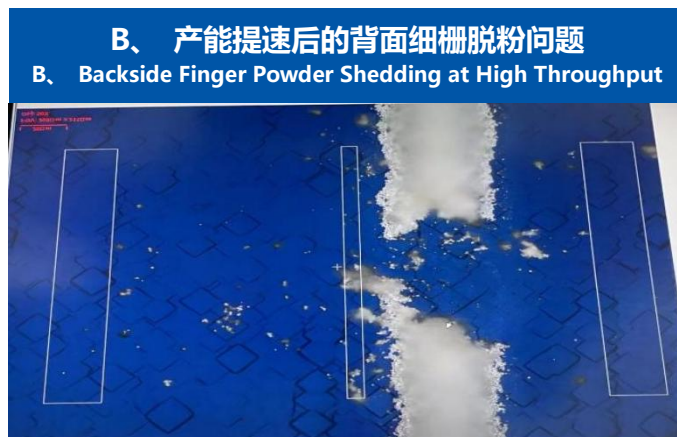
背面细栅的痛点解决：

Backside Finger Defect Solutions



适配窄线宽的有机体系，印刷后的细线趋于平整化、边缘光滑，高低起伏小

Narrow-line compatible organic system enables flat, smooth-edged printed fingers with low height variation.



针对性调整背面有机，降低表面摩擦系数，大大提高背面细栅的耐摩擦能力

Customized backside organic formulation lowers surface friction, delivering superior abrasion resistance for back fingers.

适用场景 Application

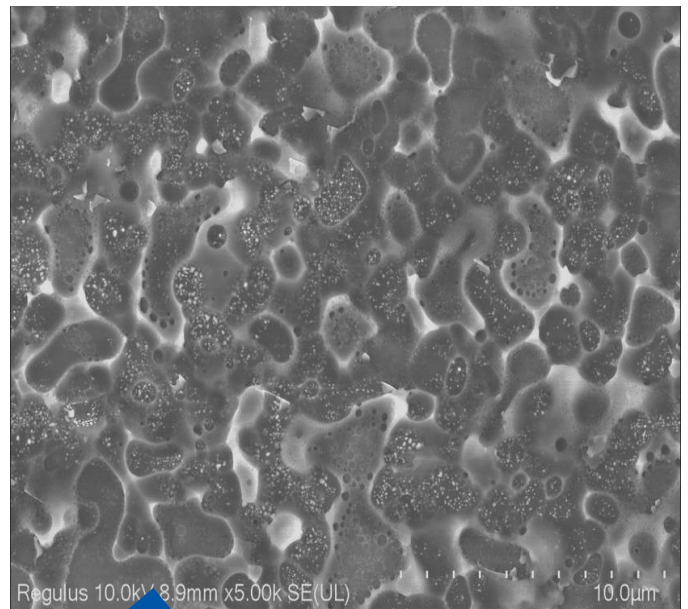
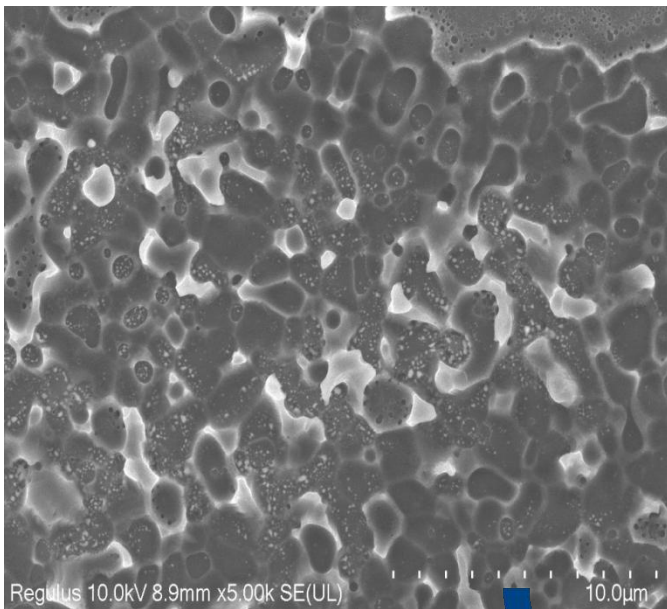
适用于 N 型硅片衬底的背接触结构，核心优势在于与 Poly 硅层形成优异的欧姆接触
Applicable to back-contact structure of N-type silicon substrate, featuring superior ohmic contact with poly-Si layer.

印刷网版 Printing screen

适配 PI 无网结超细线网版、钢版等
PI knotless screen with ultra fine line finger pattern

亮点 Highlight

- 精准活化Poly表面、生成银微晶接触点，构建低阻导电通道
Precisely activate Poly surface to form silver microcrystal contacts and build low-resistance conductive paths.
- 烧结窗口宽、可靠性好，可有效提升电池转换效率与长期稳定性
Broad firing window and excellent reliability, effectively improving cell conversion efficiency and long-term stability.
- 兼具优良的印刷流变性、适配 BC 电池细线化
Combines excellent printing rheology and adapts to fine-line printing for BC cells.
- 低银耗降本，兼顾量产良率与经济性
Low silver consumption reduces cost, balancing mass production yield and economic efficiency.



N 区优化无机配方，减薄界面玻璃层，降低接触电阻率，减少复合

Optimized inorganic formulation for N-region to thin the interfacial glass layer, reduce contact resistivity and minimize recombination.